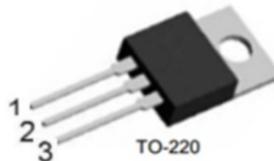


Features

- Ultra Low Forward Voltage Drop
- Excellent High Temperature Stability
- Patented Super Barrier Rectifier Technology
- Soft, Fast Switching Capability

Mechanical Data

- Case: TO-220AB,
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208



MAXIMUM RATINGS($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	VALUE	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	45	V
Maximum rms voltage	V_{RMS}	31.5	V
Maximum average forward rectified current per device per diode	$I_{F(AV)}$	20 10	A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load	I_{FSM}	150	A
Typical junction capacitance ($V_R=4\text{V}$, $f=1\text{MHz}$)	C_J	860	pF
Typical thermal resistance per diode (Note 1)	R_{eJC}	2	$^\circ\text{C}/\text{W}$
Operating junction temperature range	T_J	-55 to + 150	$^\circ\text{C}$
Storage temperature range	T_{STG}	-55 to + 150	$^\circ\text{C}$

Note : 1. Mounted on infinite heatsink.

ELECTRICAL CHARACTERISTICS($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Breakdown voltage per diode	V_{BR}	$I_R=0.5\text{mA}$	45	-	-	V
Instantaneous forward voltage per diode	V_F	$I_F=1\text{A}$ $I_F=5\text{A}$ $I_F=10\text{A}$ $T_J=25^\circ\text{C}$	-	0.30 0.38 0.45	- - 0.50	V
		$I_F=1\text{A}$ $I_F=5\text{A}$ $I_F=10\text{A}$ $T_J=125^\circ\text{C}$	-	0.20 0.31 0.39	- - -	V
		$V_R=36\text{V}$	-	100	-	μA
	I_R	$V_R=45\text{V}$ $T_J=25^\circ\text{C}$	-	-	100	μA
		$T_J=125^\circ\text{C}$	-	35	-	mA

RATING AND CHARACTERISTIC CURVES

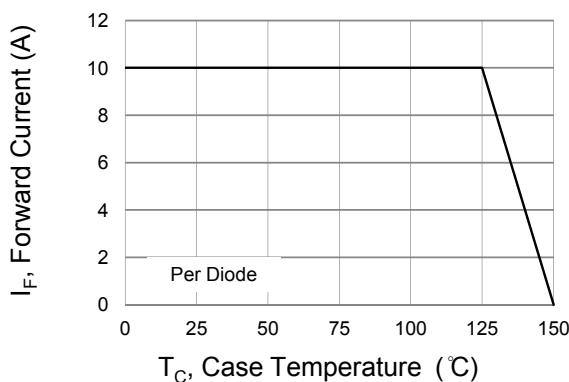


Fig.1 Forward Current Derating Curve

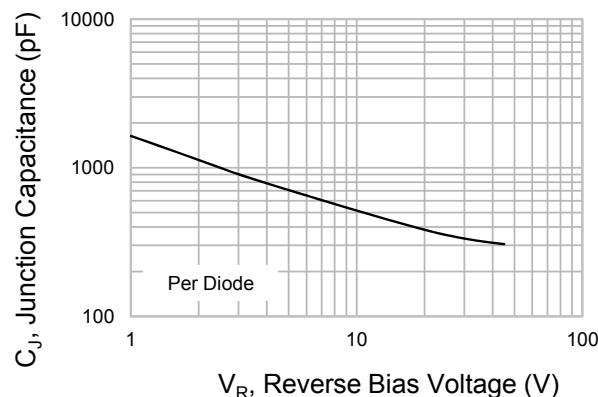


Fig.2 Typical Junction Capacitance

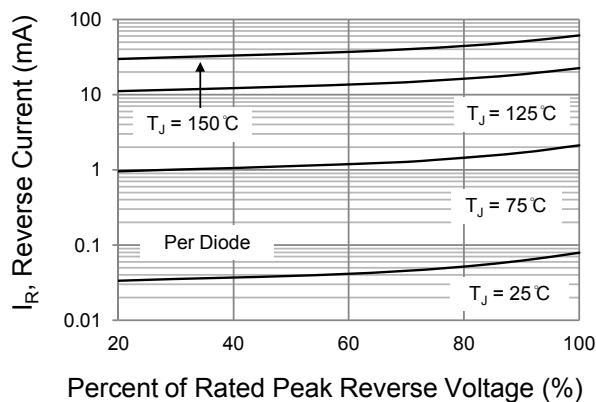


Fig.3 Typical Reverse Characteristics

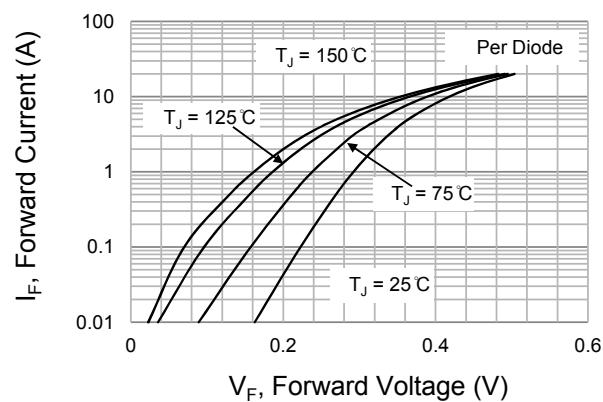


Fig.4 Typical Forward Characteristics